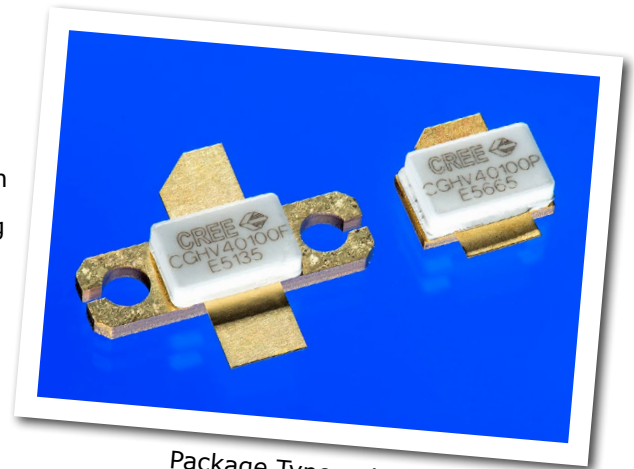


# CGHV40100

**100 W, DC - 4.0 GHz, 50 V, GaN HEMT**

Cree's CGHV40100 is an unmatched, gallium nitride (GaN) high electron mobility transistor (HEMT). The CGHV40100, operating from a 50 volt rail, offers a general purpose, broadband solution to a variety of RF and microwave applications. GaN HEMTs offer high efficiency, high gain and wide bandwidth capabilities making the CGHV40100 ideal for linear and compressed amplifier circuits. The transistor is available in a 2-lead flange and pill package.



Package Types: 440193 & 440206  
PN: CGHV40100F & CGHV40100P

## Typical Performance Over 500 MHz - 2.5 GHz ( $\tau_c = 25^\circ\text{C}$ ), 50 V

Parameter	500 MHz	1.0 GHz	1.5 GHz	2.0 GHz	2.5 GHz	Units
Small Signal Gain	17.6	16.9	17.7	17.5	14.8	dB
Saturated Output Power	147	100	141	116	112	W
Drain Efficiency @ $P_{SAT}$	68	56	58	54	54	%
Input Return Loss	6	5.1	10.5	5.5	8.8	dB

Note:  
Measured CW in the CGHV40100F-TB application circuit.

## Features

- Up to 4 GHz Operation
- 100 W Typical Output Power
- 17.5 dB Small Signal Gain at 2.0 GHz
- Application Circuit for 0.5 - 2.5 GHz
- 55 % Efficiency at  $P_{SAT}$
- 50 V Operation



Large Signal Models Available for SiC & GaN



## Absolute Maximum Ratings (not simultaneous) at 25 °C Case Temperature

Parameter	Symbol	Rating	Units	Conditions
Drain-Source Voltage	$V_{DSS}$	125	Volts	25 °C
Gate-to-Source Voltage	$V_{GS}$	-10, +2	Volts	25 °C
Storage Temperature	$T_{STG}$	-65, +150	°C	
Operating Junction Temperature	$T_J$	225	°C	
Maximum Forward Gate Current	$I_{GMAX}$	20.8	mA	25 °C
Maximum Drain Current <sup>1</sup>	$I_{DMAX}$	8.7	A	25 °C
Soldering Temperature <sup>2</sup>	$T_S$	245	°C	
Screw Torque	$\tau$	40	in-oz	
Thermal Resistance, Junction to Case <sup>3</sup>	$R_{\theta JC}$	1.62	°C/W	85 °C
Thermal Resistance, Junction to Case <sup>4</sup>	$R_{\theta JC}$	1.72	°C/W	85 °C
Case Operating Temperature <sup>5</sup>	$T_C$	-40, +150	°C	30 seconds

Note:

<sup>1</sup> Current limit for long term, reliable operation

<sup>2</sup> Refer to the Application Note on soldering at [www.cree.com/products/wireless\\_appnotes.asp](http://www.cree.com/products/wireless_appnotes.asp)

<sup>3</sup> Measured for the CGHV40100P at  $P_{DISS} = 83$  W.

<sup>4</sup> Measured for the CGHV40100F at  $P_{DISS} = 83$  W.

<sup>5</sup> See also, Power Derating Curve on Page 7

## Electrical Characteristics ( $T_C = 25$ °C)

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
<b>DC Characteristics<sup>1</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	-3.8	-3.0	-2.3	$V_{DC}$	$V_{DS} = 10$ V, $I_D = 20.8$ mA
Gate Quiescent Voltage	$V_{GS(Q)}$	-	-2.7	-	$V_{DC}$	$V_{DS} = 50$ V, $I_D = 0.6$ A
Saturated Drain Current <sup>2</sup>	$I_{DS}$	15.6	18.7	-	A	$V_{DS} = 6.0$ V, $V_{GS} = 2.0$ V
Drain-Source Breakdown Voltage	$V_{BR}$	150	-	-	$V_{DC}$	$V_{GS} = -8$ V, $I_D = 20.8$ mA
<b>RF Characteristics<sup>3</sup> (<math>T_C = 25</math> °C, <math>F_0 = 2.0</math> GHz unless otherwise noted)</b>						
Small Signal Gain	$G_{SS}$	-	17.5	-	dB	$V_{DD} = 50$ V, $I_{DQ} = 0.6$ A
Power Gain	$G_P$	-	11.0	-	dB	$V_{DD} = 50$ V, $I_{DQ} = 0.6$ A, $P_{OUT} = P_{SAT}$
Power Output at Saturation <sup>4</sup>	$P_{SAT}$	-	116	-	W	$V_{DD} = 50$ V, $I_{DQ} = 0.6$ A
Drain Efficiency	$\eta$	-	54	-	%	$V_{DD} = 50$ V, $I_{DQ} = 0.6$ A, $P_{OUT} = P_{SAT}$
Output Mismatch Stress	VSWR	-	-	10 : 1	$\Psi$	No damage at all phase angles, $V_{DD} = 50$ V, $I_{DQ} = 0.6$ A, $P_{OUT} = 100$ W CW
<b>Dynamic Characteristics<sup>5</sup></b>						
Input Capacitance	$C_{GS}$	-	29.3	-	pF	$V_{DS} = 50$ V, $V_{GS} = -8$ V, $f = 1$ MHz
Output Capacitance	$C_{DS}$	-	7.3	-	pF	$V_{DS} = 50$ V, $V_{GS} = -8$ V, $f = 1$ MHz
Feedback Capacitance	$C_{GD}$	-	0.61	-	pF	$V_{DS} = 50$ V, $V_{GS} = -8$ V, $f = 1$ MHz

Notes:

<sup>1</sup> Measured on wafer prior to packaging.

<sup>2</sup> Scaled from PCM data.

<sup>3</sup> Measured in CGHV40100-TB.

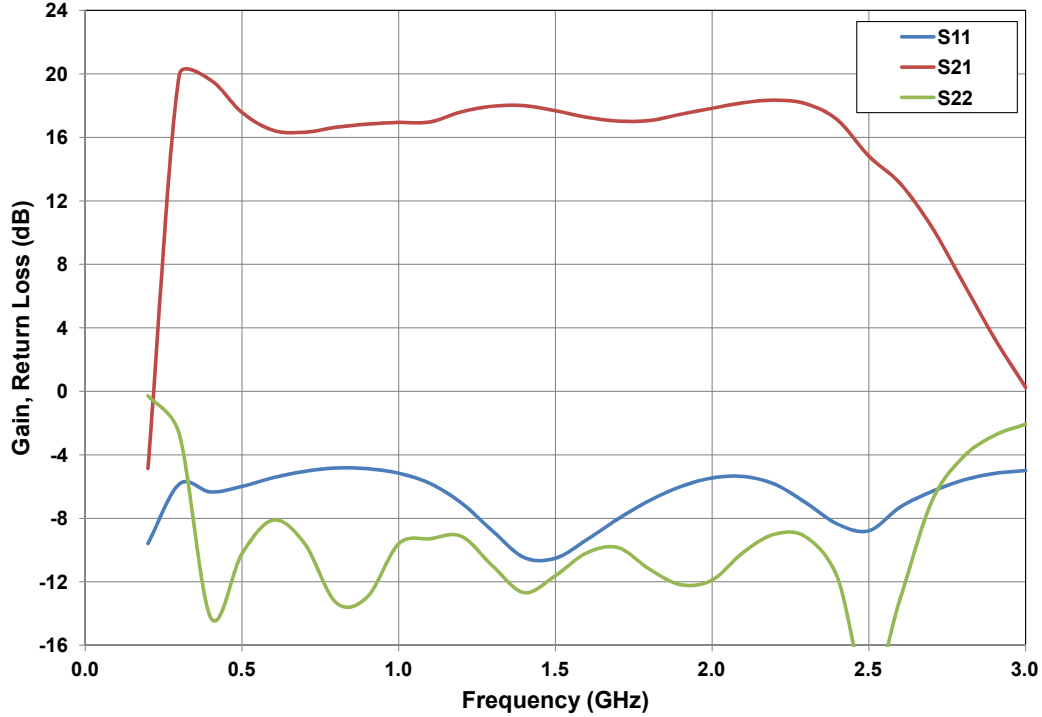
<sup>4</sup>  $P_{SAT}$  is defined as  $I_G$

<sup>5</sup> Includes package

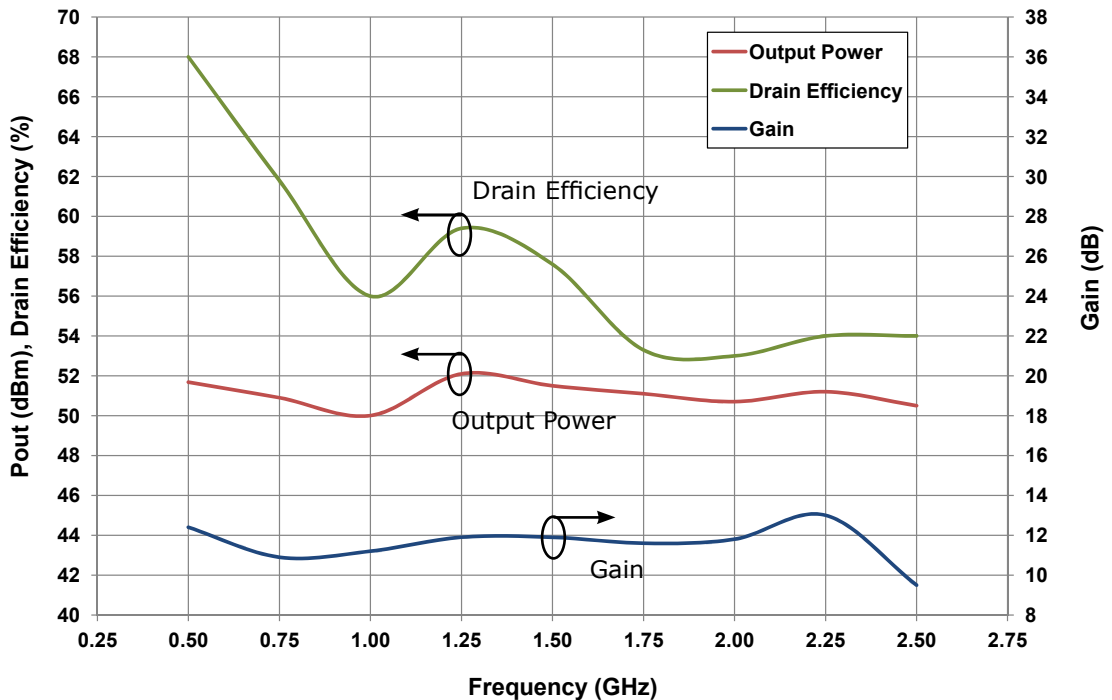


## CGHV40100 Typical Performance

**Figure 1. - Small Signal Gain and Return Losses versus Frequency of the CGHV40100 in the application circuit CGHV40100-TB**  
 $V_{DD} = 50\text{ V}$ ,  $I_{DQ} = 600\text{ mA}$ ,  $T_{case} = 25^\circ\text{C}$



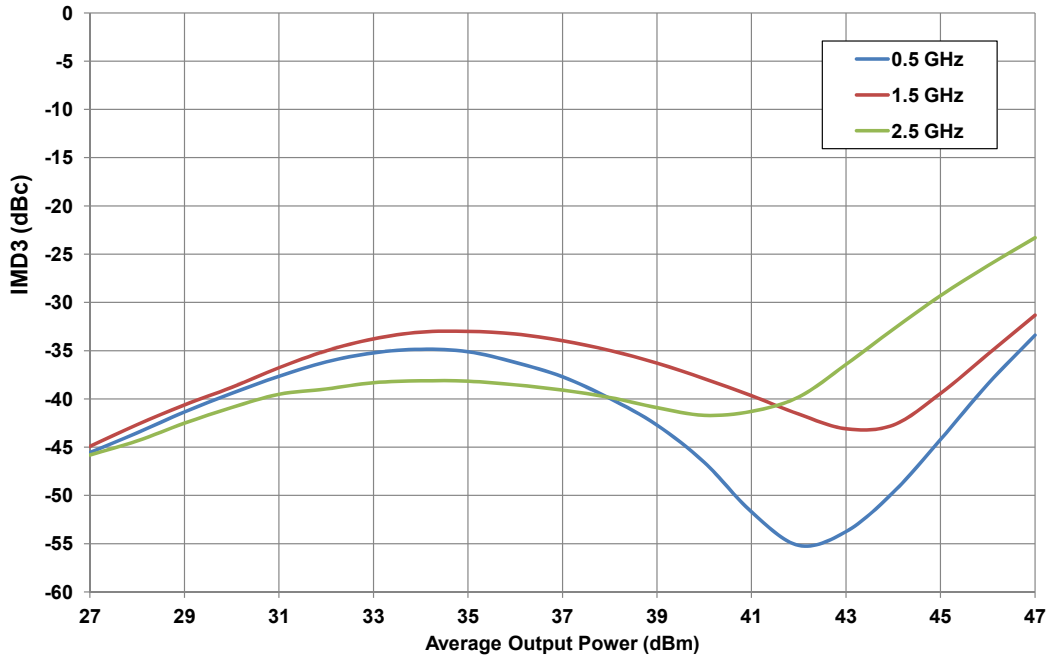
**Figure 2. - Output Power and Drain Efficiency vs Frequency**  
 $V_{DD} = 50\text{ V}$ ,  $I_{DQ} = 600\text{ mA}$



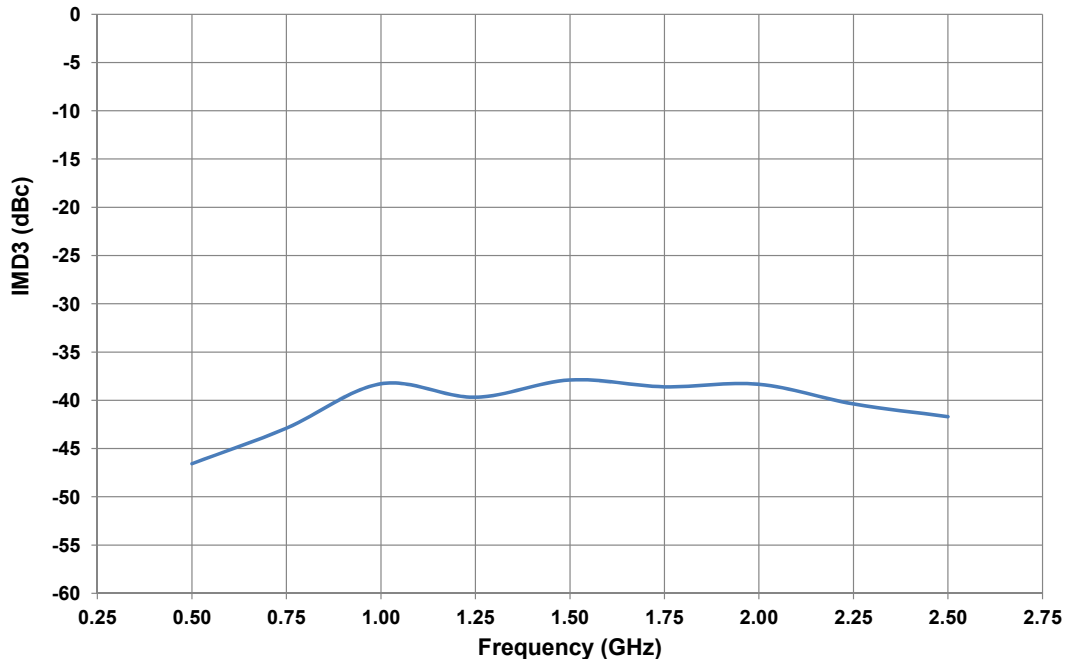


## CGHV40100 Typical Performance

**Figure 3. - Third Order Intermodulation Distortion vs Average Output Power of CGHV40100 measured in Broadband Amplifier Circuit CGHV40100-TB**  
Spacing = 1 MHz,  $V_{DD} = 50\text{ V}$ ,  $I_{DQ} = 600\text{ mA}$ ,  $T_{case} = 25^\circ\text{C}$



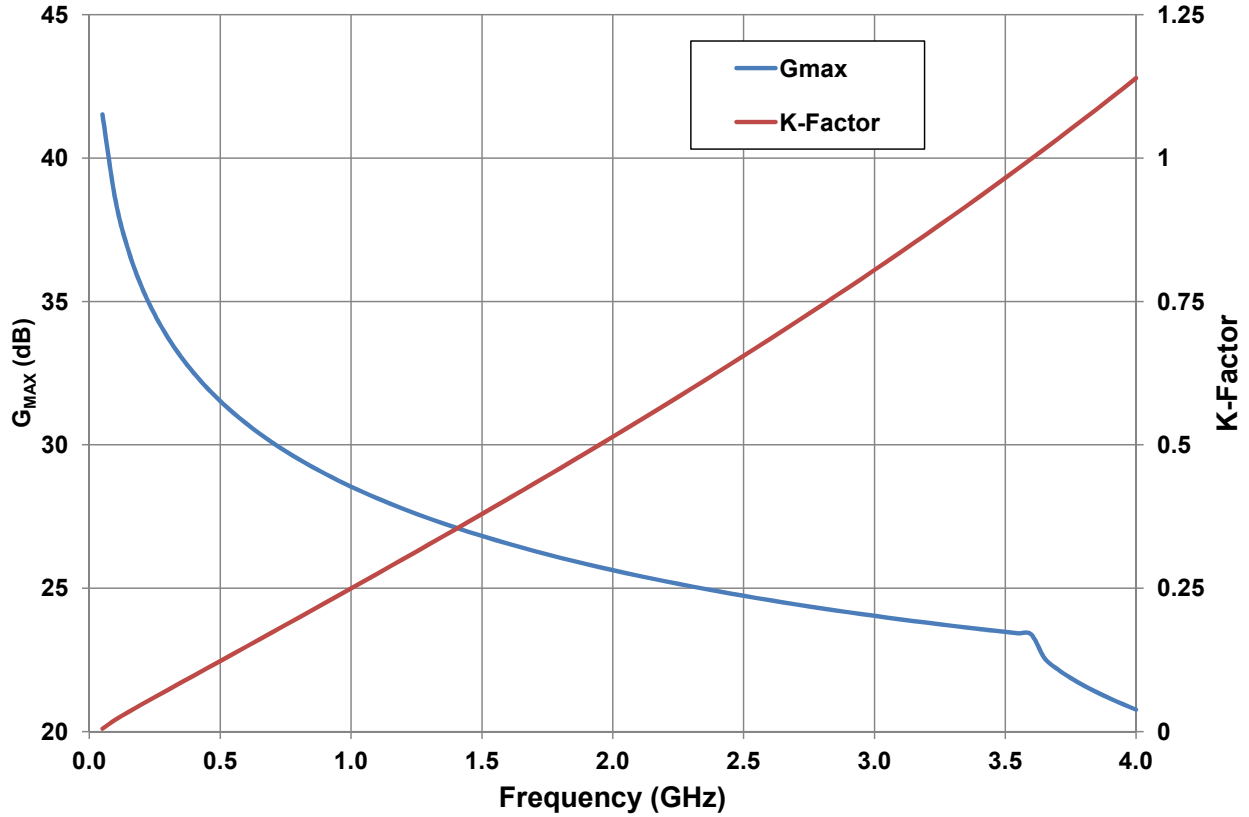
**Figure 4. - Third Order Intermodulation Distortion vs Frequency of CGHV40100 measured in Broadband Amplifier Circuit CGHV40100-TB**  
Spacing = 1 MHz,  $V_{DD} = 50\text{ V}$ ,  $I_{DQ} = 600\text{ mA}$ ,  $T_{case} = 25^\circ\text{C}$



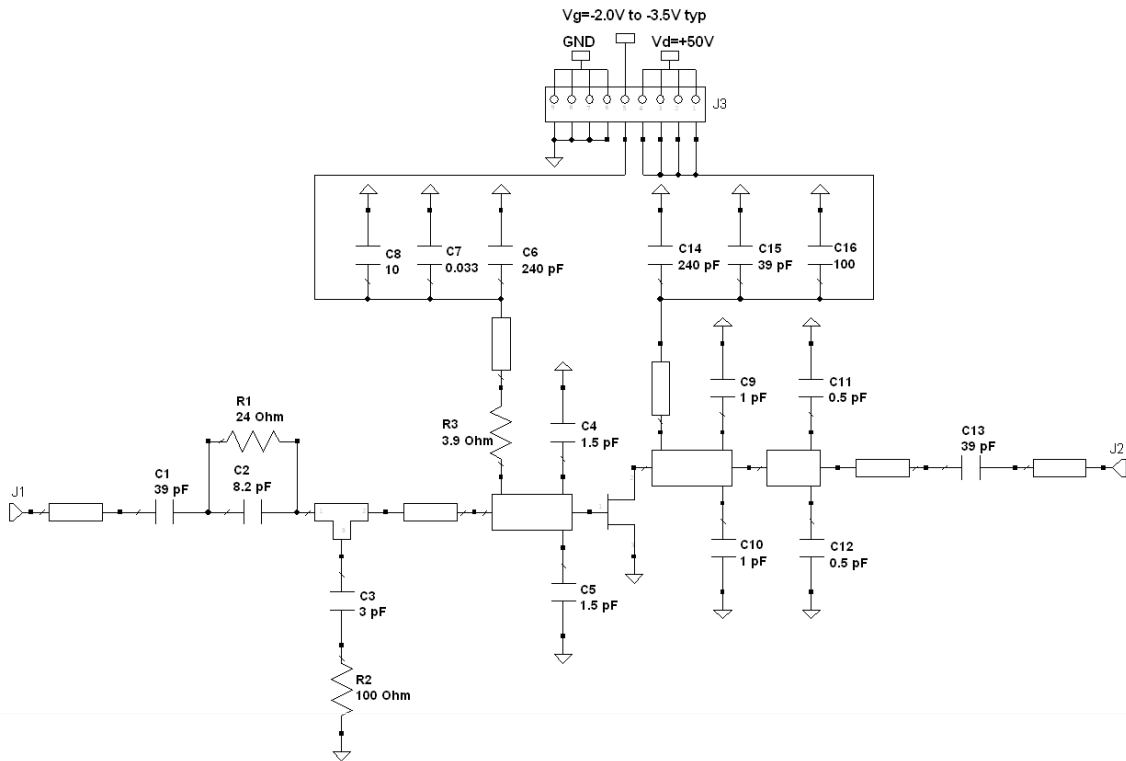


## CGHV40100 Typical Performance

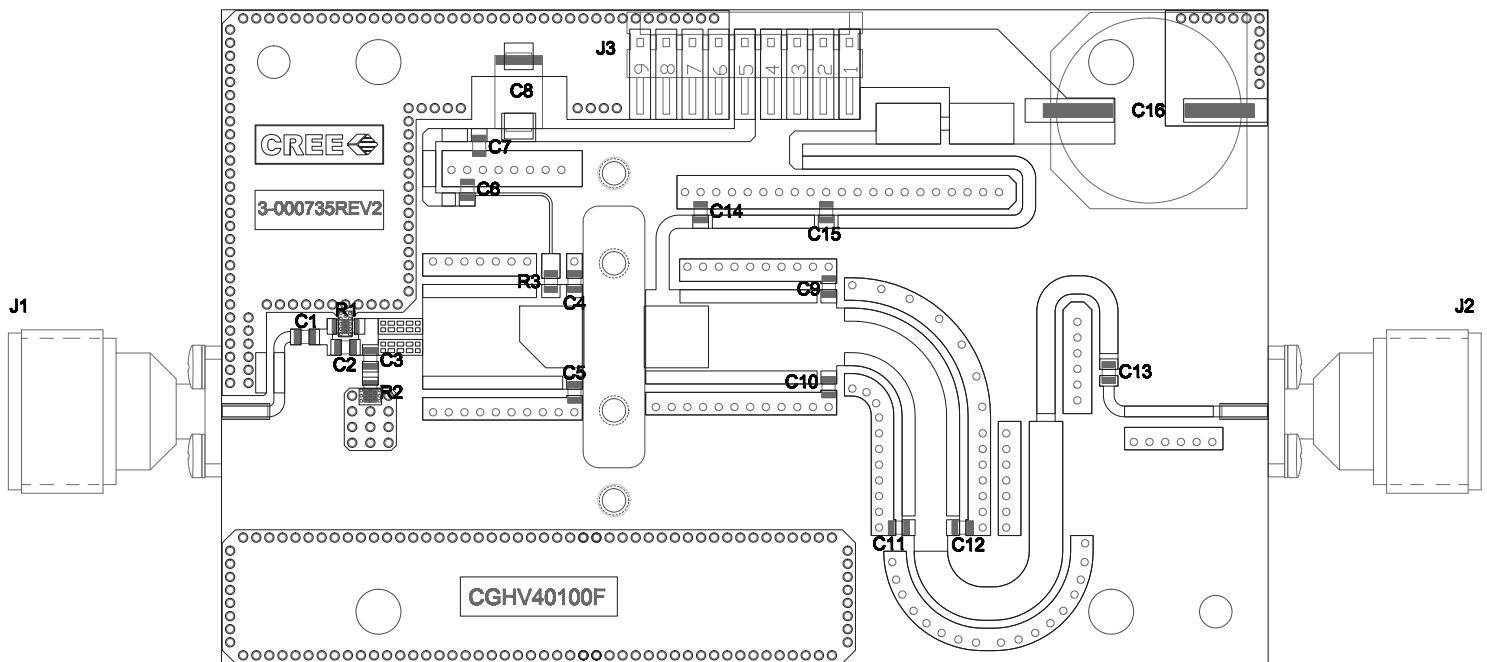
Figure 5. -  $G_{MAX}$  and K-Factor vs Frequency  
 $V_{DD} = 50\text{ V}$ ,  $I_{DQ} = 600\text{ mA}$ ,  $T_{case} = 25^\circ\text{C}$



## CGHV40100-TB Application Circuit Schematic



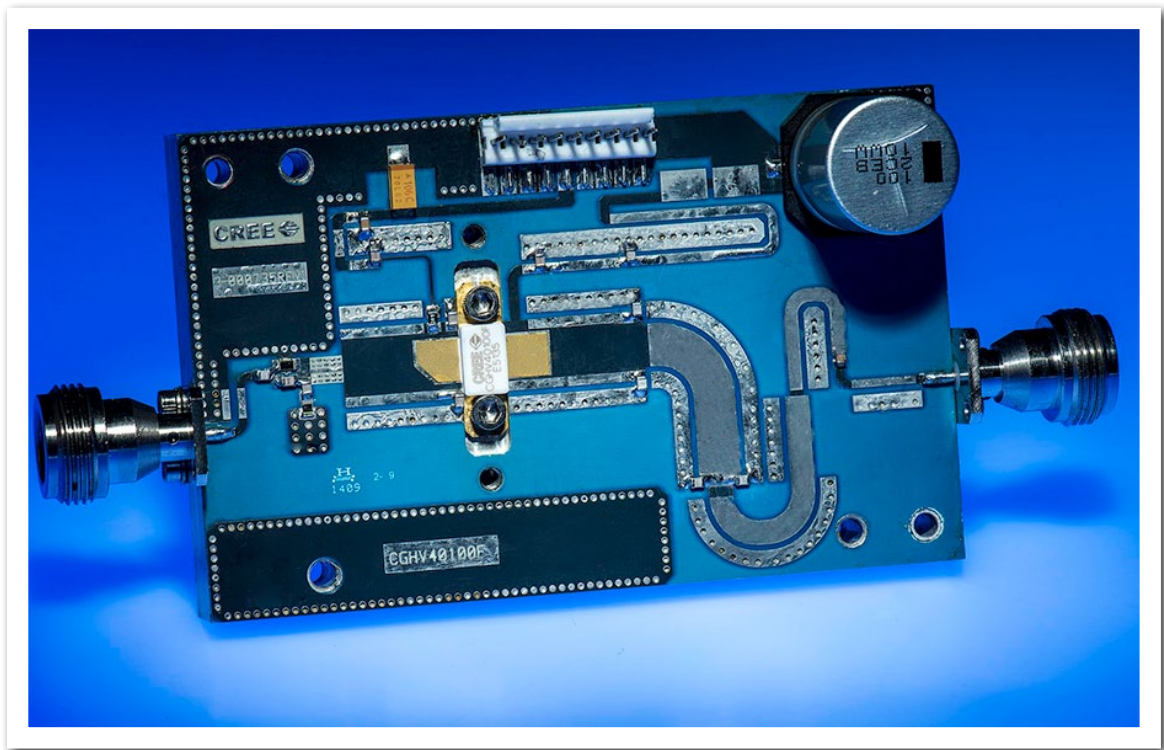
## CGHV40100-TB Application Circuit



## CGHV40100-TB Application Circuit Bill of Materials

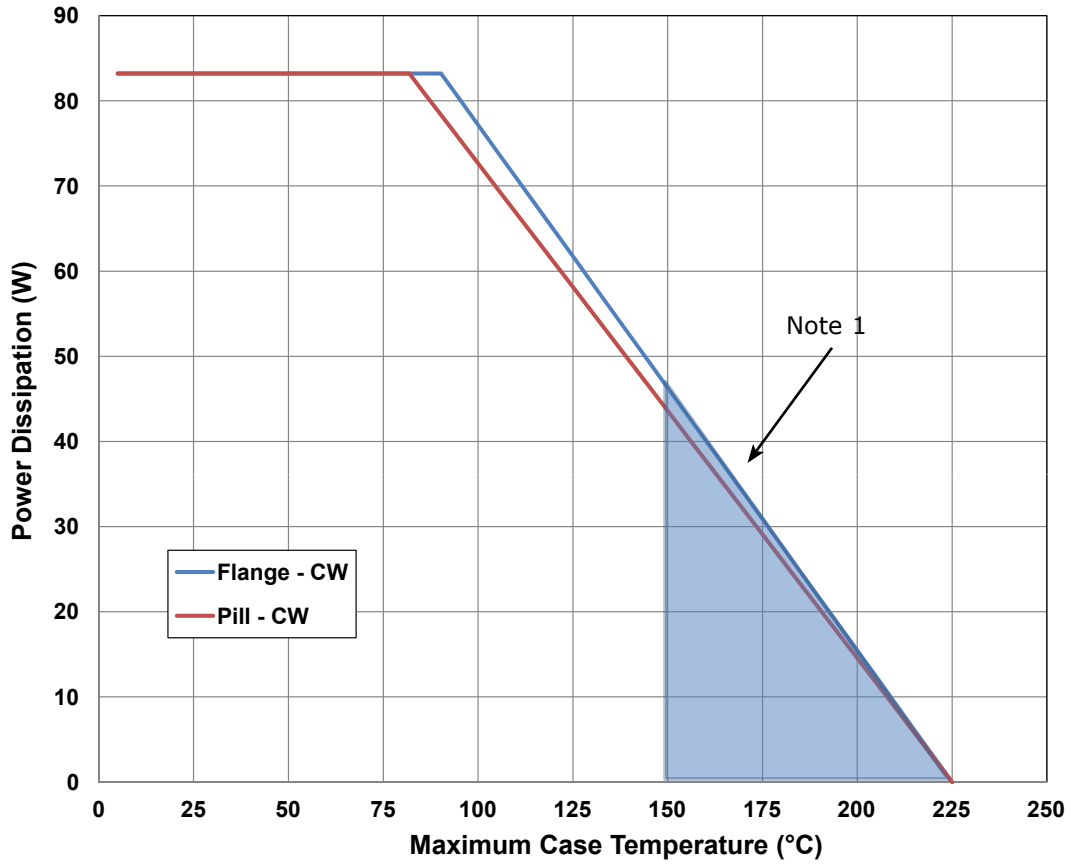
Designator	Description	Qty
C1, C13, C15	CAP, 39 pF, $\pm 0.1$ pF, 250V, 0805, ATC600F	3
C2	CAP, 8.2 pF, $\pm 0.1$ pF, 250 V, 0806, ATC600F	1
C3	CAP, 3 pF $\pm 0.1$ pF, 250 V, 0805, ATC600F	1
C4, C5	CAP, 1.5 pF, $\pm 0.1$ pF, 250 V, 0805, ATC600F	2
C7	CAP, 33000 pF, 0805 100V, X7R	1
C6, C14	CAP, 240 pF, $\pm 0.5$ pF, 250 V, 0805, ATC600F	2
C8	CAP, 10 UF, 16V TANTALUM, 2312	1
C9, C10	CAP, 1 pF, $\pm 0.1$ pF, 250 V, 0805, ATC600F	2
C11, C12	CAP, 0.5 pF, $\pm 0.1$ pF, 250 V, 0805, ATC600F	2
C16	CAP, 100 UF, 20%, 160 V, ELEC	1
R1	RES, 24 OHMS, IMS ND3-1005CS24R0G	1
R2	RED, 100 OHMS, IMS ND3-0805EW1000G	1
R3	RES, 3.9 OHMS, 0805	1
J1, J2	CONN, N, FEM, W/.500 SMA FLNG	2
J3	HEADER RT>PLZ .1CEN LK 9POS	1
	BASEPLATE, CGH35120	1
	PCB, RO4350B, 2.5" X 4" X 0.020", CGHV40100F	1

## CGHV40100-TB Demonstration Amplifier Circuit



# CGHV40100 Power Dissipation De-rating Curve

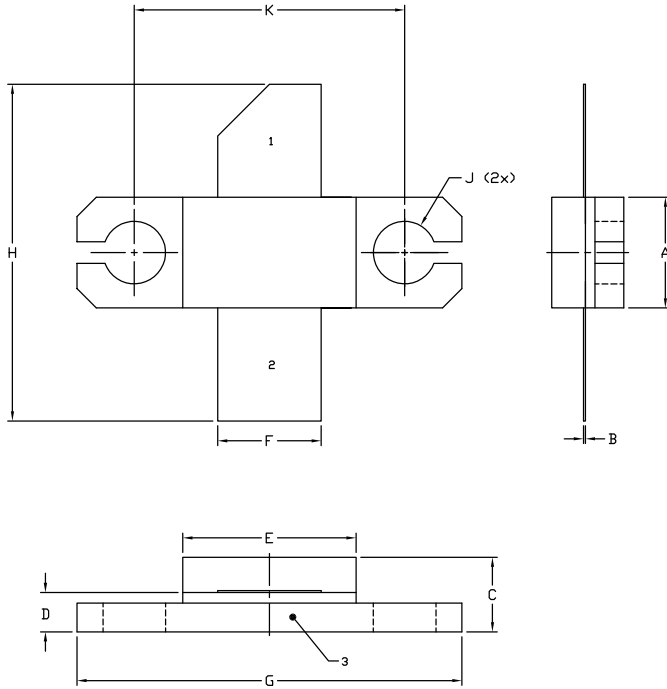
Figure 5. - Transient Power Dissipation De-Rating Curve



Note 1. Area exceeds Maximum Case Temperature (See Page 2).



## Product Dimensions CGHV40100F (Package Type — 440193)

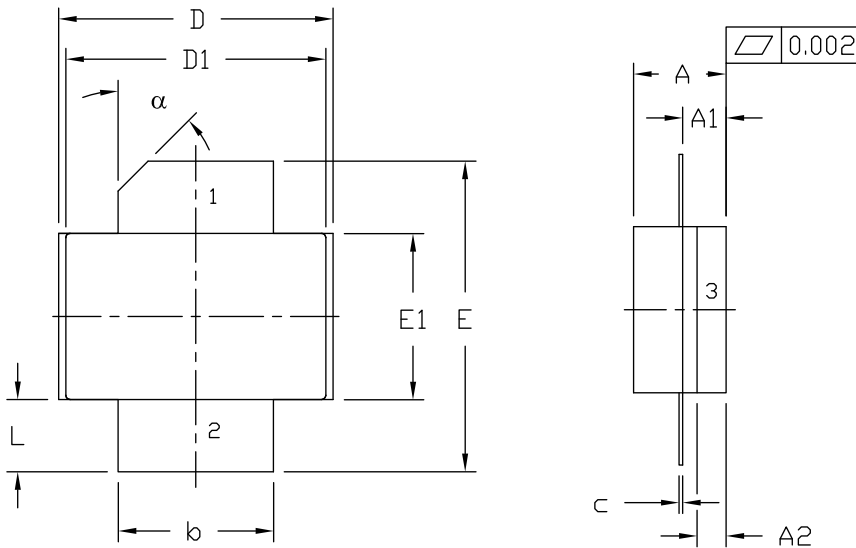


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
  4. LID MAY BE MISALIGNED TO THE BODY OF THE PACKAGE BY A MAXIMUM OF 0.008" IN ANY DIRECTION.
  5. ALL PLATED SURFACES ARE Ni/AU.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.225	0.235	5.72	5.97
B	0.004	0.006	0.10	0.15
C	0.145	0.165	3.68	4.19
D	0.077	0.087	1.96	2.21
E	0.355	0.365	9.02	9.27
F	0.210	0.220	5.33	5.59
G	0.795	0.805	20.19	20.45
H	0.670	0.730	17.02	18.54
J	∅ .130		3.30	
k	0.562		14.28	

- PIN 1. GATE  
 PIN 2. DRAIN  
 PIN 3. SOURCE

## Product Dimensions CGHV40100P (Package Type — 440206)



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M - 1994.
  2. CONTROLLING DIMENSION: INCH.
  3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
  4. LID MAY BE MISALIGNED TO THE BODY OF PACKAGE BY A MAXIMUM OF 0.008" IN ANY DIRECTION.

DIM	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.125	0.145	3.18	3.68	
A1	0.057	0.067	1.45	1.70	
A2	0.035	0.045	0.89	1.14	
b	0.210	0.220	5.33	5.59	2x
c	0.004	0.006	0.10	0.15	2x
D	0.375	0.385	9.53	9.78	
D1	0.355	0.365	9.02	9.27	
E	0.400	0.460	10.16	11.68	
E1	0.225	0.235	5.72	5.97	
L	0.085	0.115	2.16	2.92	2x
α	45° REF		45° REF		

- PIN 1. GATE  
 PIN 2. DRAIN  
 PIN 3. SOURCE



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- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



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